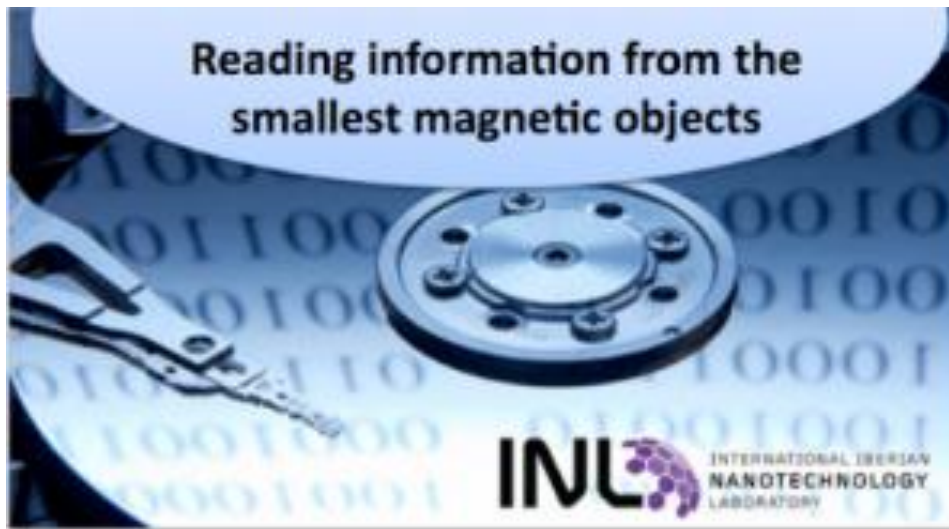


PROBING THE NUCLEAR SPIN OF A SINGLE DONOR IN SILICON NANOTRANSISTORS

F. Delgado* and J. Fernández-Rossier

*Email: fernando.delgado@inl.int

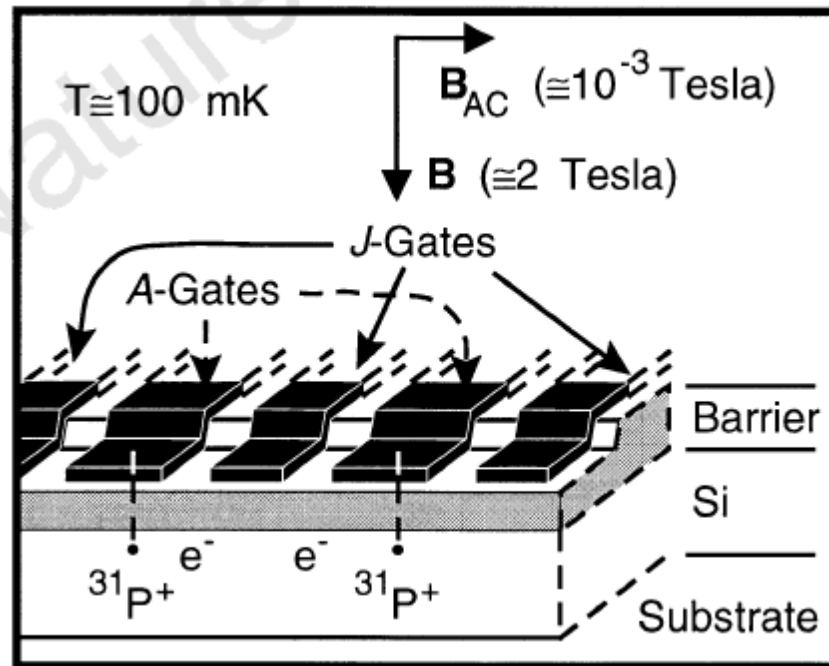
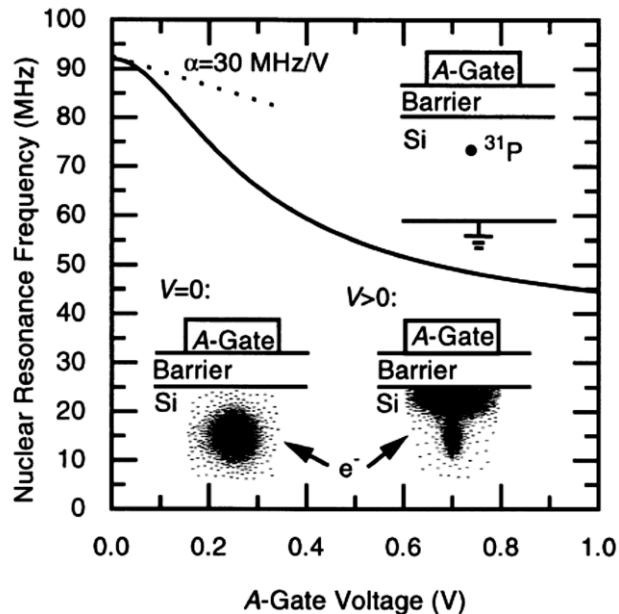


A silicon-based nuclear spin quantum computer

B. E. Kane

Semiconductor Nanofabrication Facility, School of Physics, University of New South Wales, Sydney 2052, Au

From B. E. Kane, Nature (1998).



Advantages:

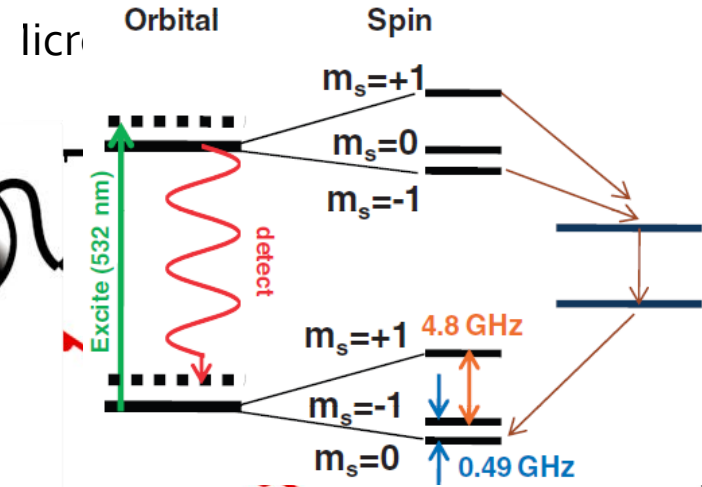
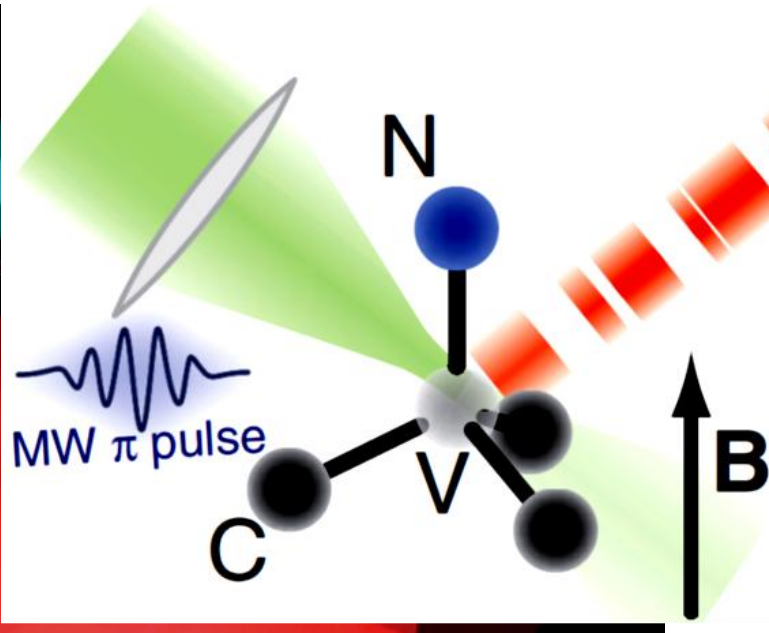
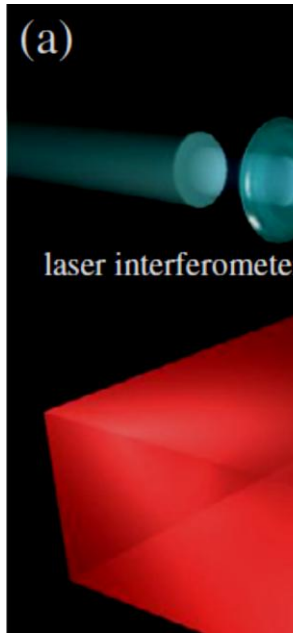
- High isolated qubits
- Long coherence/relaxation times ($\sim 10 \text{ ms}$)
- Scalable systems

- MRFM
- OD-MR

OD-MR (Optically Detected Magnetic Resonance)

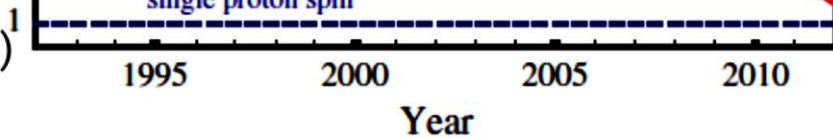
(Single nuclear spin detection)

NV centers in diamond



G. D. Fuchs *et al.*, Science (2009)
le electron spin

D. Rugar *et al.*, Nature (2004)
P. Neumann *et al.*, Science (2010)



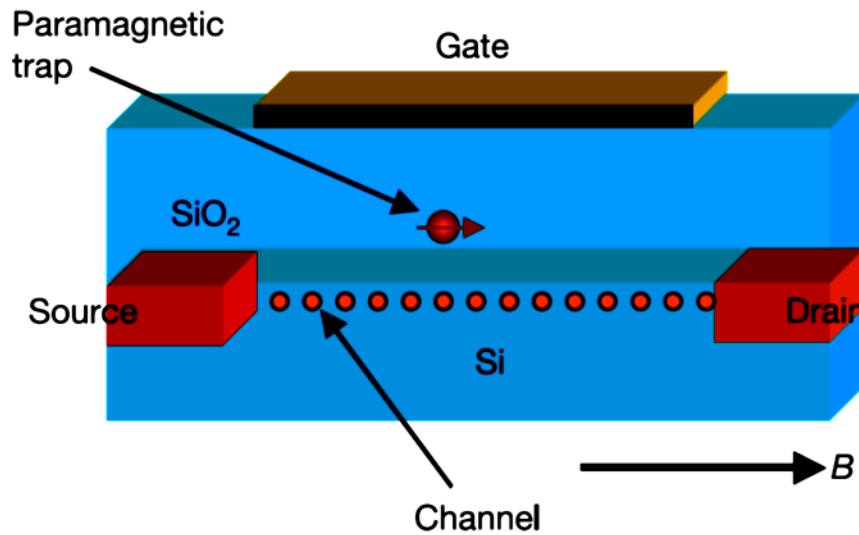
M. Poggio & C. L. Degen *et al.*,
Nanotechnology (2010)

Transport- based detection

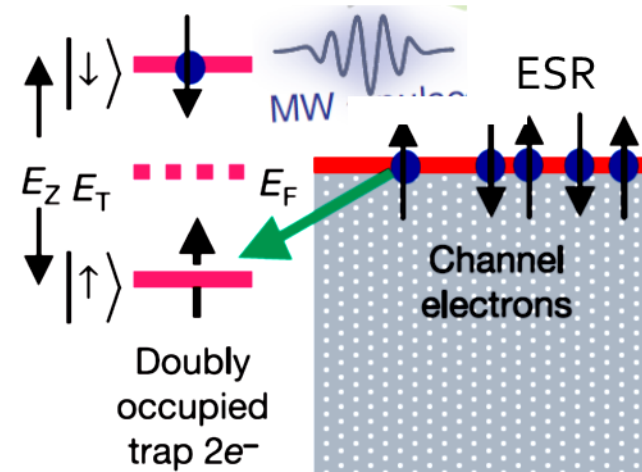
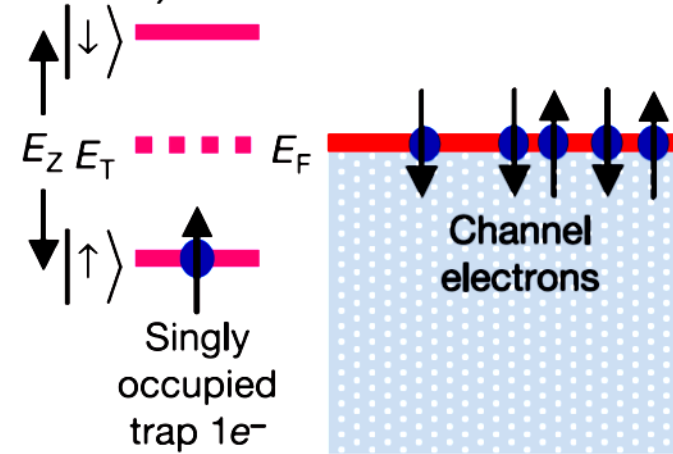
- EDMR

EDMR (Electrically Detected Magnetic Resonance)
(spin-to-charge conversion)

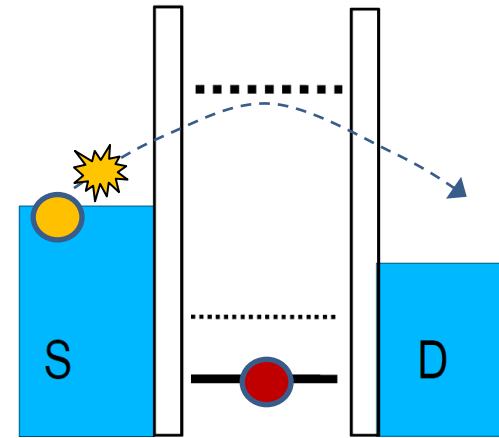
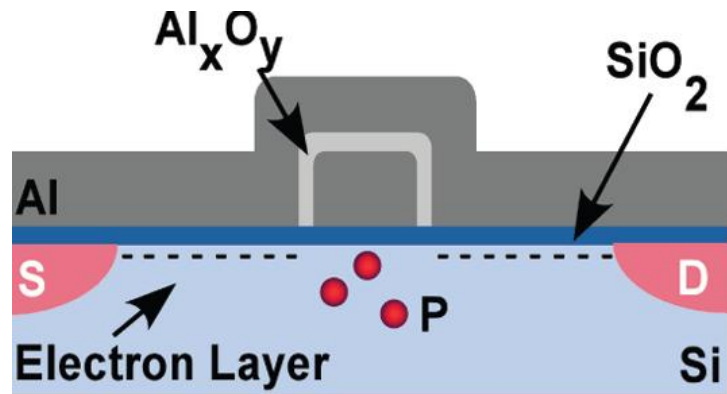
(demonstrated single spin detection)



M. Xiao *et al.*, Nature(2004)

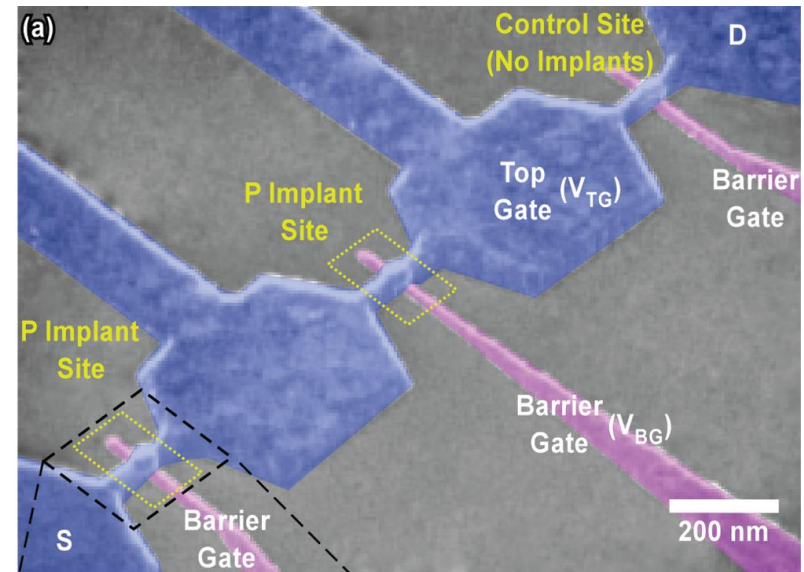
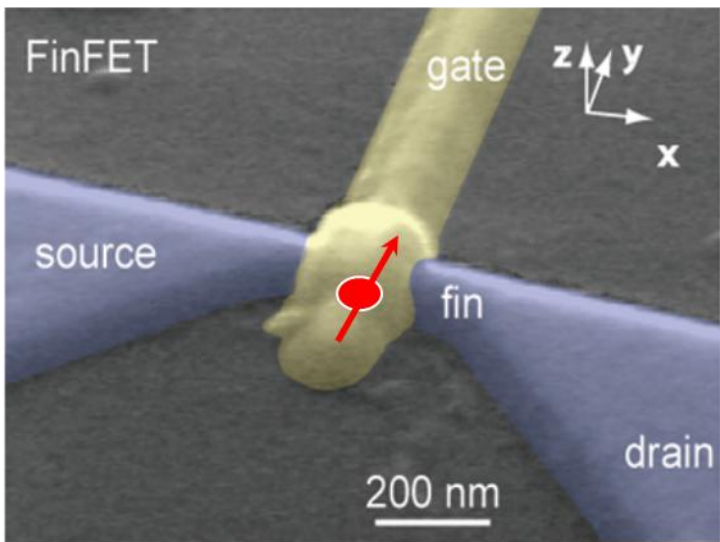


SINGLE DOPANT Si NANOTRANSISTORS

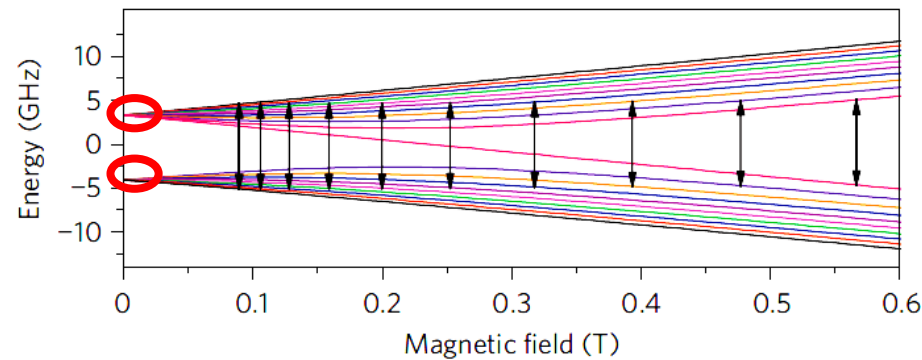
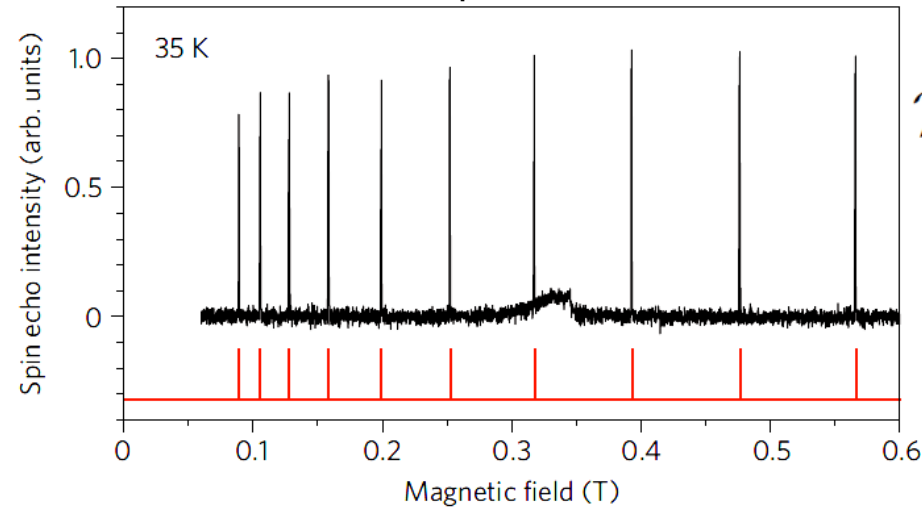


G. P. Lansbergen *et al.*, Nano (2010).

K. Yen Tan *et al.*, Nano (2009).



ESR spectrum

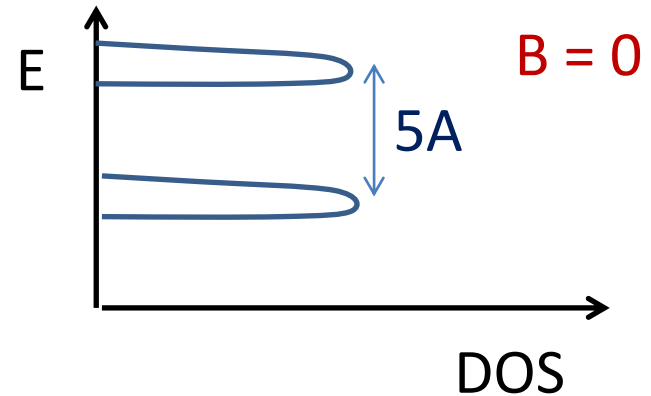


Electro-nuclear system

$$\mathcal{H}_{\text{Spin}} = A\vec{I} \cdot \vec{S} + (g\mu_B\vec{S} + g\mu_I\vec{I}) \cdot \vec{B}$$

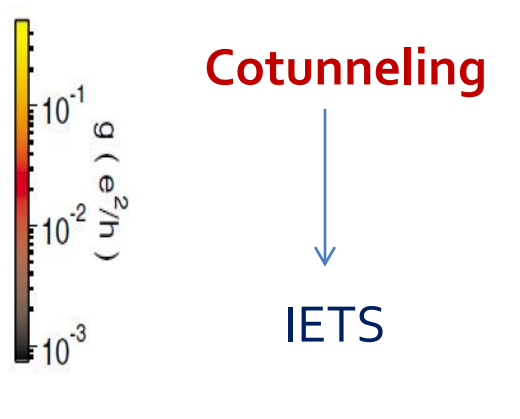
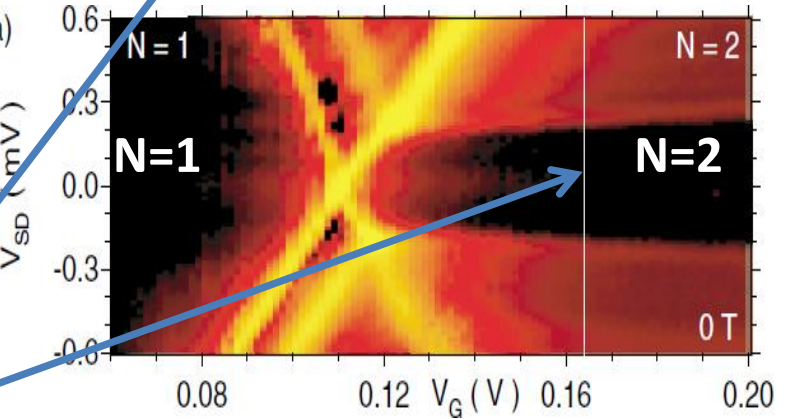
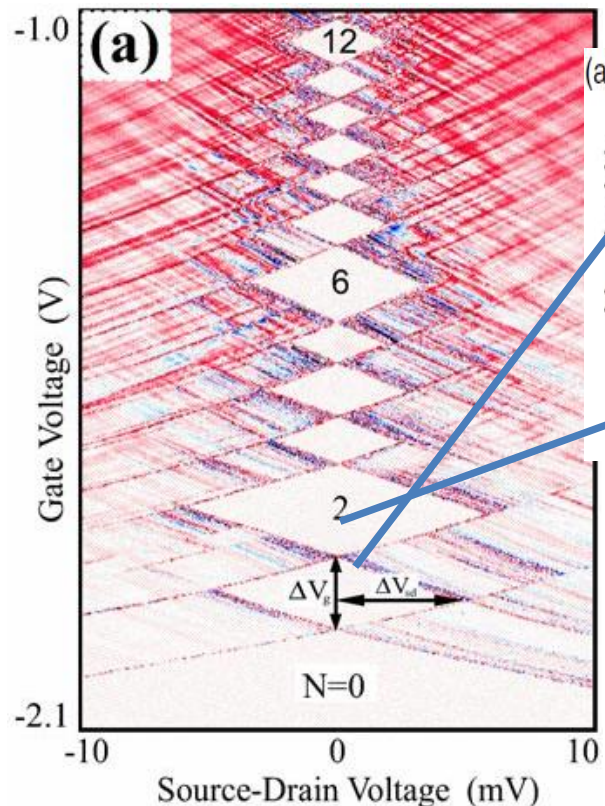
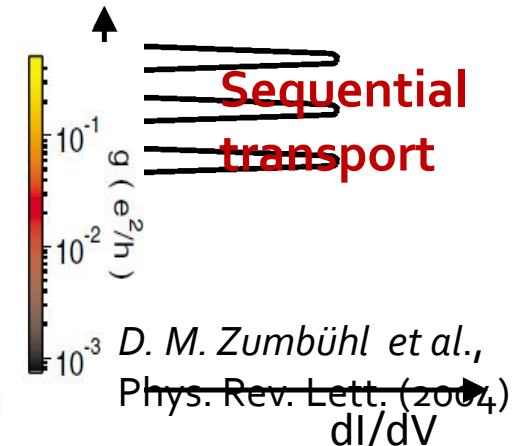
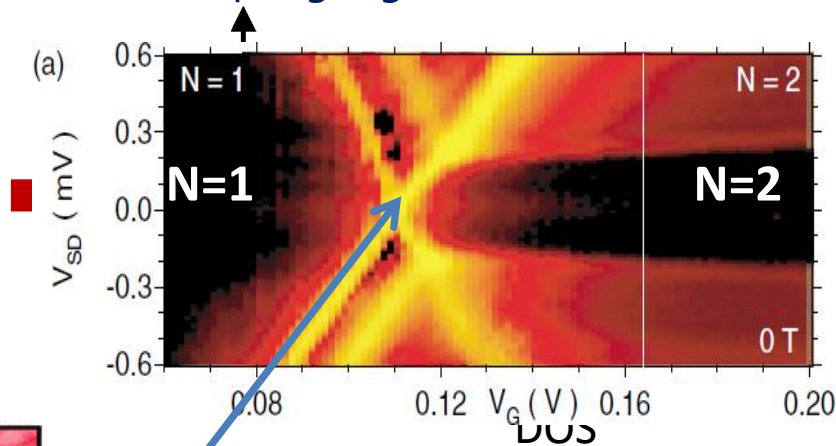
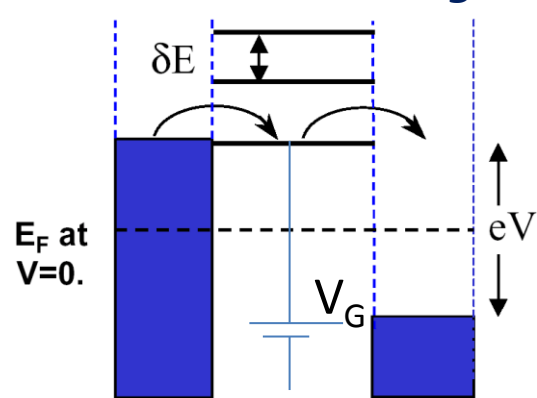
$$I = 9/2 \quad \& \quad S = 1/2 \quad \& \quad A = 6.1\mu\text{eV}$$

$$\vec{F} = \vec{S} + \vec{I} \longrightarrow F = 4, 5$$

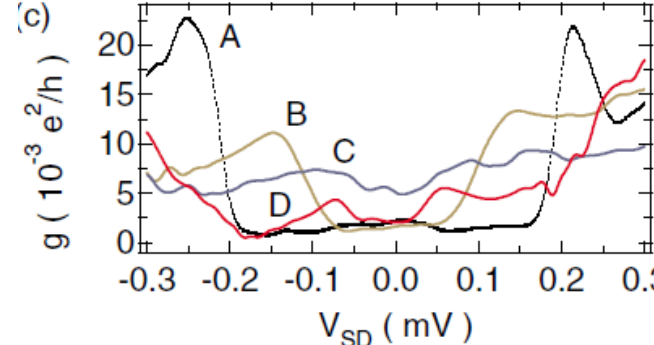


- G. W. Morley *et al.*, Nature Materials (2010)
- R. E. George *et al.*, Phys. Rev. Lett. (2010)

Coulomb blockade regime (Weak coupling regime)



L. P. Kouwenhoven *et al.*,
Rep. Prog. Phys. (2001)



Total Hamiltonian

$$\mathcal{H}_T = \mathcal{H}_{Spin} + V_g \sum_{\sigma} n_{\sigma} + \mathcal{H}_S + \mathcal{H}_D + \mathcal{V}$$

Free electron reservoirs

$$\mathcal{H}_S + \mathcal{H}_D = \sum_{k\eta\sigma} \epsilon_{k\eta\sigma} c_{k\eta\sigma}^{\dagger} c_{k\eta\sigma}$$

Electro-nuclear spin system

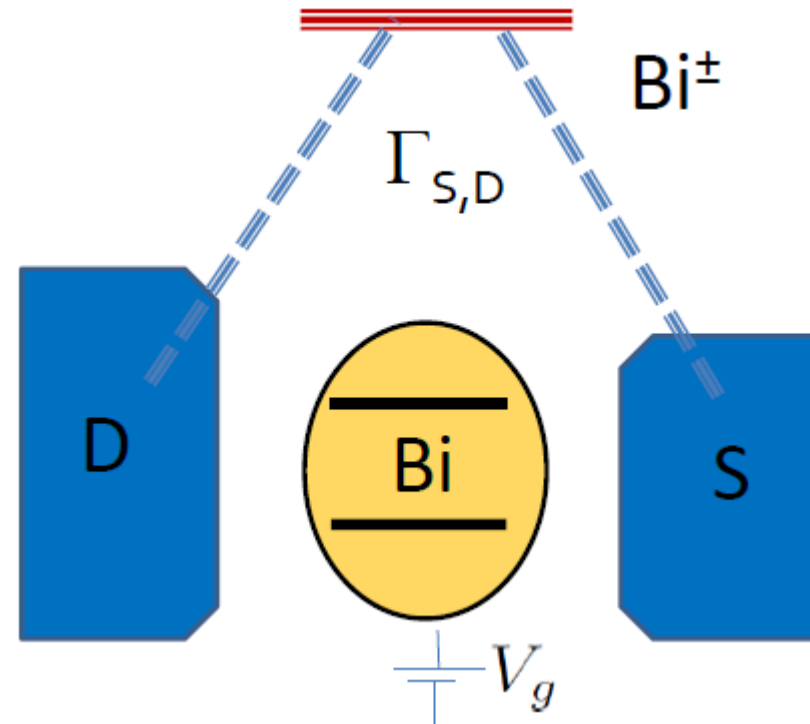
$$\mathcal{H}_{Spin} + V_g \sum_{\sigma} n_{\sigma}$$

Tunneling Hamiltonian (Perturbation)

- **Consequential transport** (1st order in \mathcal{V})

$$\Gamma_{M,M'}^{cot} \propto |\langle M | \mathcal{V}_{eff} | \dots | M' \rangle|^2$$

$$\mathcal{V}_{eff} = J \vec{s} \cdot \vec{S} + W$$



Sequential transport

- Charge fluctuations: $Q_{Bi} = 0, 1 e^-$

- Current

$$I^{seq} = e \sum_{\alpha_0, \alpha_1} \left(P_{\alpha_0}(V) W_{\alpha_0, \alpha_1}^{S \rightarrow Bi} - P_{\alpha_1} W_{\alpha_1, \alpha_0}^{Bi \rightarrow S} \right)$$

Non-equilibrium populations

$$\frac{dP_{\alpha_i}(V)}{dt} = 0 \quad (\text{Steady state condition})$$

P_{α_0} : Occupation probability of $0e^-$ state α_0

P_{α_1} : Occupation probability of $1e^-$ state α_1

Cotunneling transport

- Negligible charge fluctuations

$$\mathcal{V}_{eff} = J \vec{s} \cdot \vec{S} + W$$

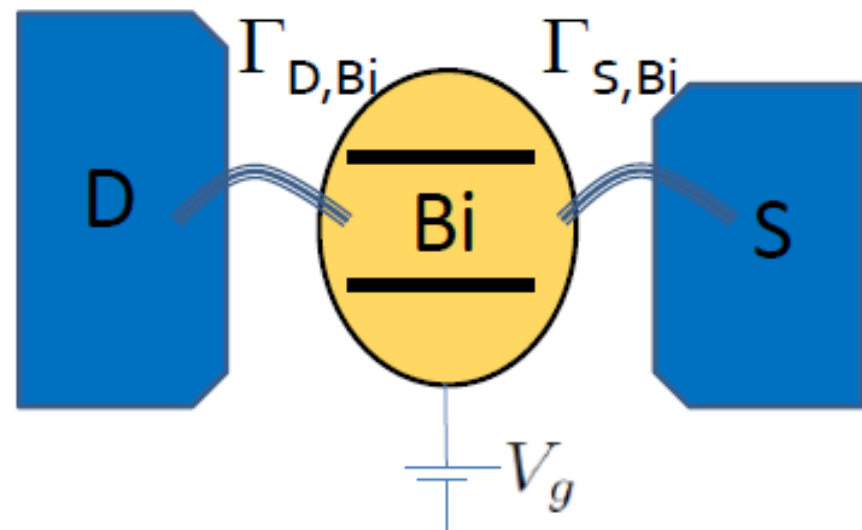
- Current

$$I^{cot} = e \sum_{M, M'} P_M(V) (W_{M, M'}^{StoD} - W_{M, M'}^{D \rightarrow S})$$

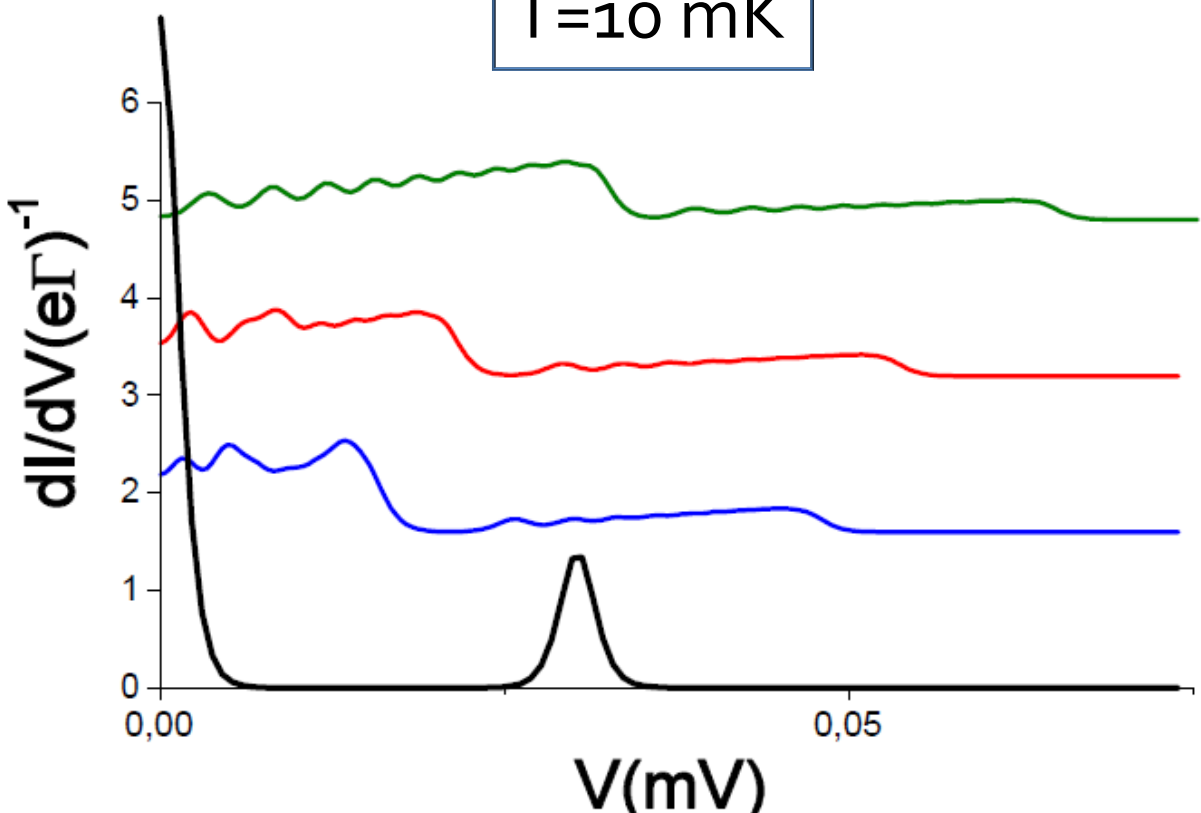
Non-equilibrium populations

$$\frac{dP_M(V)}{dt} = 0 \quad (\text{Steady state condition})$$

SEQUENTIAL TRANSPORT REGIME

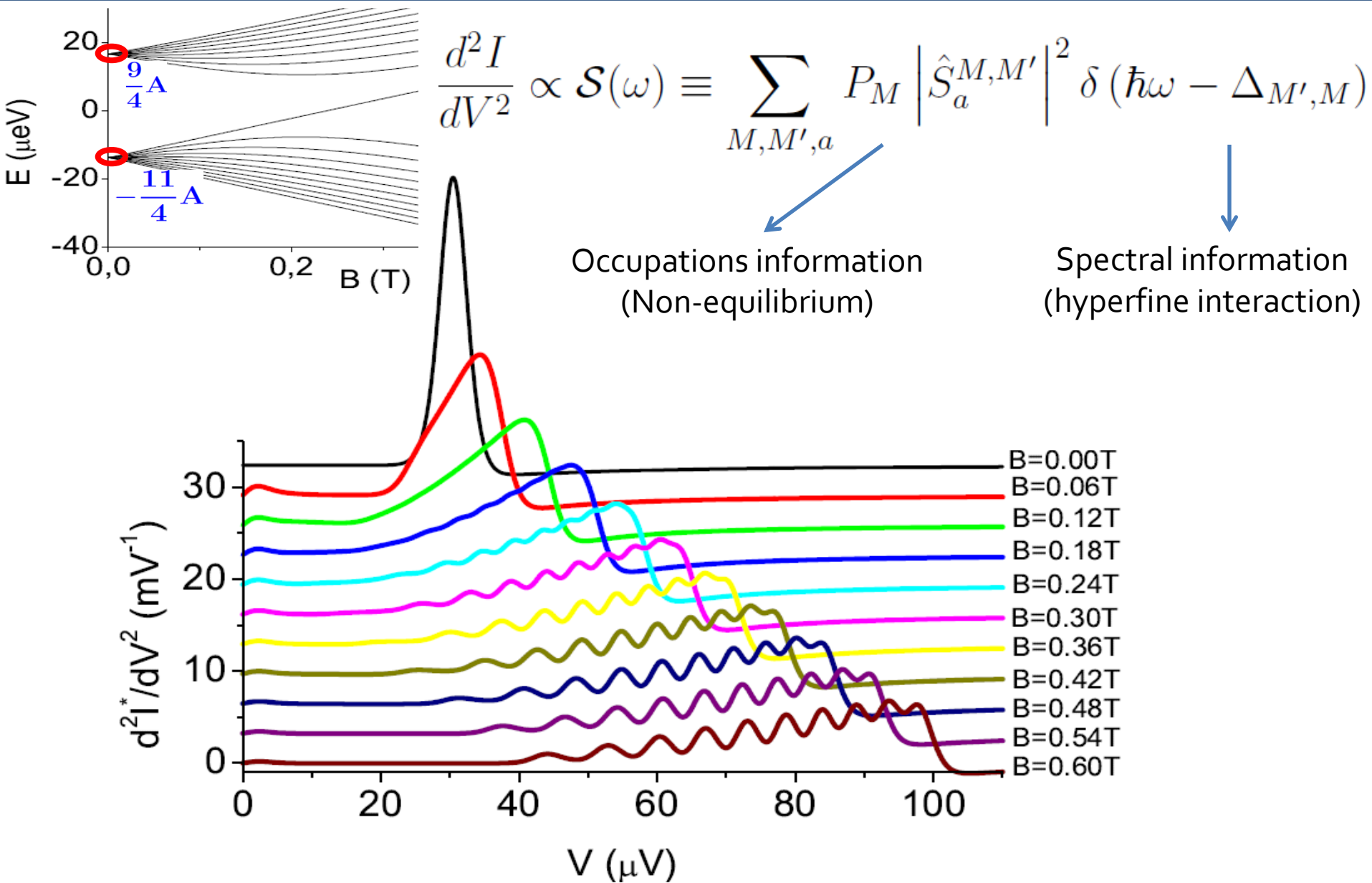


$T=10$ mK



- B**
- 0.6 T
 - 0.4 T
 - 0.2 T
 - 0 T

IETS: COTUNNELING REGIME



- Si:Bi nanotransistors are good candidates to probe nuclear spins due to the large hyperfine coupling in Bi ($A \gg k_B T$)
- Hyperfine structure can be probed in the sequential or in the cotunneling regime
- Single nuclear spins can be probed by IETS.

ACKNOWLEDGMENTS



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INL, Braga, Portugal

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**THANK YOU
FOR YOUR
ATTENTION !!!**



Departamento de Física Aplicada
Universidad de Alicante



